

# Schottky barrier diode

## RB451F

### ●Applications

Low power rectification

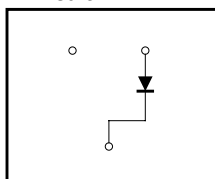
### ●Features

- 1) Small surface mounting type. (UMD3)
- 2) Low  $V_F$ . ( $V_F=0.45V$  Typ. at 100mA)
- 3) High reliability.

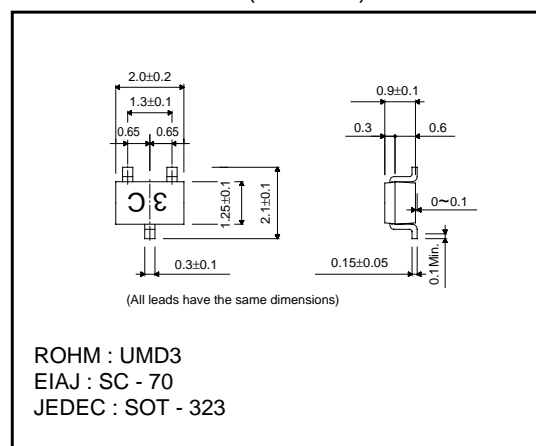
### ●Construction

Silicon epitaxial planar

### ●Circuit



### ●External dimensions (Units : mm)



### ●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	$V_{RM}$	40	V
DC reverse voltage	$V_R$	40	V
Mean rectifying current	$I_o$	0.1	A
Peak forward surge current*	$I_{FSM}$	1	A
Junction temperature	$T_j$	125	°C
Storage temperature	$T_{stg}$	-40~+125	°C

\* 60Hz for 1  $\varnothing$

### ●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	$V_{F1}$	-	-	0.55	V	$I_F=100mA$
	$V_{F2}$	-	-	0.34	V	$I_F=10mA$
Reverse current	$I_R$	-	-	30	$\mu A$	$V_R=10V$
Capacitance between terminals	$C_T$	-	6.0	-	pF	$V_R=10V, f=1MHz$

Note) ESD sensitive product handling required.

Diodes

●Electrical characteristic curves (Ta = 25°C)

